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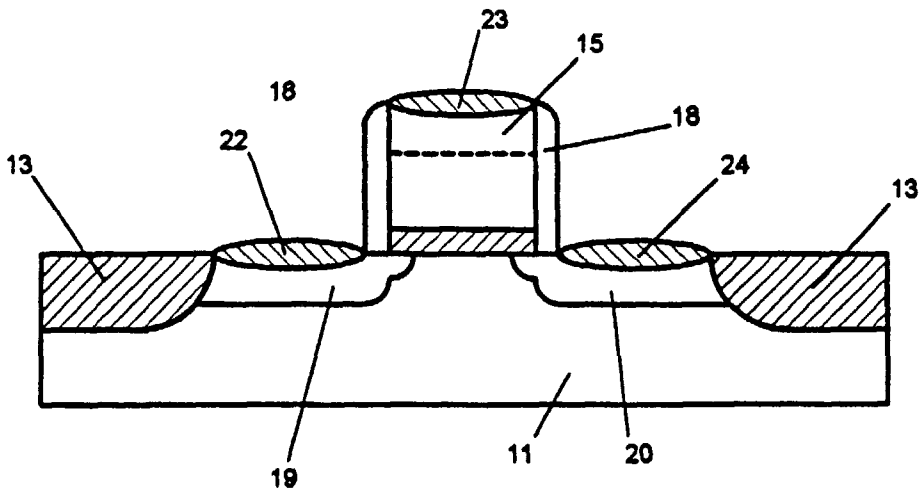
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(54) Title: IMPROVED HIGH K-DIELECTRICS USING NICKEL SILICIDE



(57) Abstract: A method for preventing the thermal decomposition of a high-K deilectric layer (12) of a gate electrode (14) during the formation of a metal silicide (22, 24) on the gate electrode (14) by using nickel as the metal component of the silicide (22, 24).

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